MOSFETs Silicon N-Channel MOS (DTMOS V)

TK560P60Y

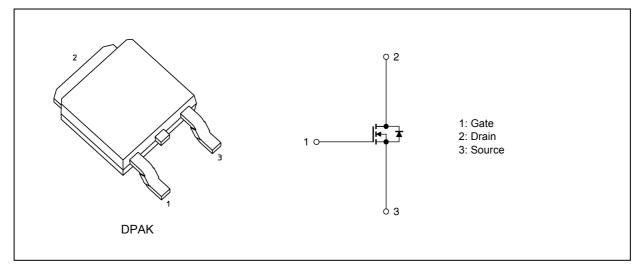
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.43 \Omega$ (typ.) by using Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
 - (3) Enhancement mode: V_{th} = 3 to 4 V (V_{DS} = 10 V, I_{D} = 0.24 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25 \ ^{\circ}C$ unless otherwise specified)

Characteristics				Rating	Unit
Drain-source voltage			V _{DSS}	600	V
Gate-source voltage			V _{GSS}	±30	7
Drain current (DC)	(T _c = 25 °C)	(Note 1)	Ι _D	7	Α
Drain current (DC)	(T _c = 100 °C)	(Note 1)	Ι _D	4.4	Α
Drain current (pulsed)	(T _c = 25 °C)	(Note 1)	I _{DP}	28	Α
Power dissipation	(T _c = 25 °C)		PD	60	W
Single-pulse avalanche energy		(Note 2)	E _{AS}	64	mJ
Single-pulse avalanche current			I _{AS}	1.8	Α
Reverse drain current (DC)		(Note 1)	I _{DR}	7	1
Reverse drain current (pulsed)		(Note 1)	I _{DRP}	28	Α
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

2016-12

5. Thermal Characteristics

Characteristics		Max	Unit
Channel-to-case thermal resistance		2.08	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	125	

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V_{DD} = 90 V, T_{ch} = 25 °C (initial), L = 34.8 mH, R_G = 25 Ω , I_{AS} = 1.8 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	_	_	±1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	600	_	_	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.24 mA	3	_	4	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 3.5 A	_	0.43	0.56	Ω

6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 300 V, V _{GS} = 0 V, f = 100 kHz	_	380	—	pF
Reverse transfer capacitance	C _{rss}		_	2.5	—	
Output capacitance	C _{oss}		_	18	—	
Effective output capacitance	C _{o(er)}	V_{DS} = 0 to 400 V, V_{GS} = 0 V	_	30	_	
Gate resistance	r _g	V _{DS} = OPEN , f = 1 MHz	-	32	_	Ω
Switching time (rise time)	tr	See Figure 6.2.1		20	_	ns
Switching time (turn-on time)	t _{on}		_	50	_	
Switching time (fall time)	t _f		_	8	_	
Switching time (turn-off time)	t _{off}		_	105	_	
MOSFET dv/dt ruggedness	dv/dt	$V_{DS} \le V_{(BR)DSS}, I_D \le 3.5 \text{ A}$	50	_	_	V/ns

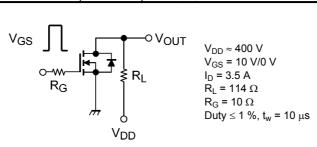


Fig. 6.2.1 Switching Time Test Circuit

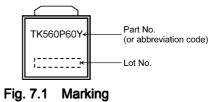
6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 7 \text{ A}$		14.5	_	nC
Gate-source charge 1	Q _{gs1}		_	2.3	_	
Gate-drain charge	Q _{gd}			7.5	_	

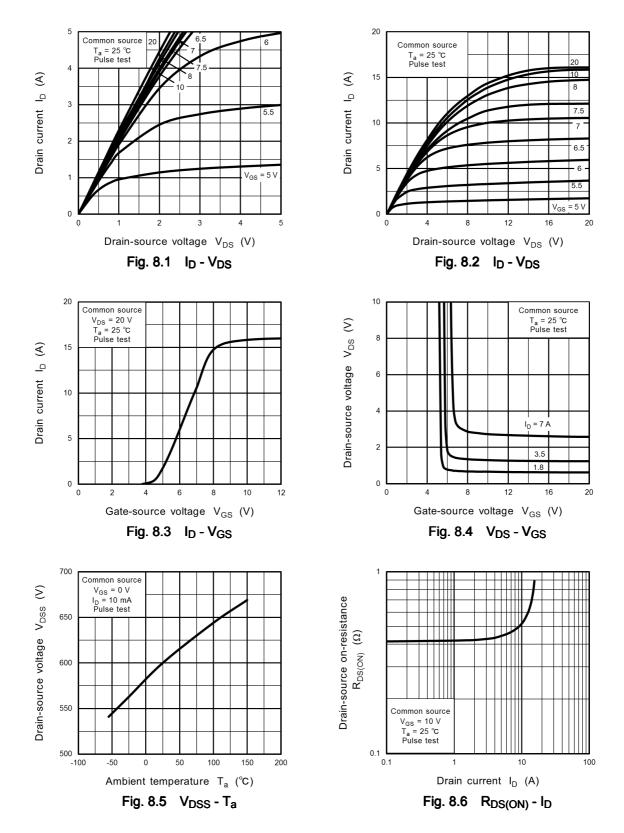
6.4. Source-Drain Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V _{DSF}	I _{DR} = 7 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	$V_{DD} \approx 400 \text{ V}$	_	240	_	ns
Reverse recovery charge	Q _{rr}	I _{DR} = 3 A, V _{GS} = 0 V -dI _{DR} /dt = 100 A/μs		1.6	_	μC
Peak reverse recovery current	l _{rr}		_	14.2	_	А
Diode dv/dt ruggedness	dv/dt	$V_{DS} \leq 400$ V, $I_{DR} \leq 3$ A, V_{GS} = 0 V	15	_	_	V/ns

7. Marking



8. Characteristics Curves (Note)



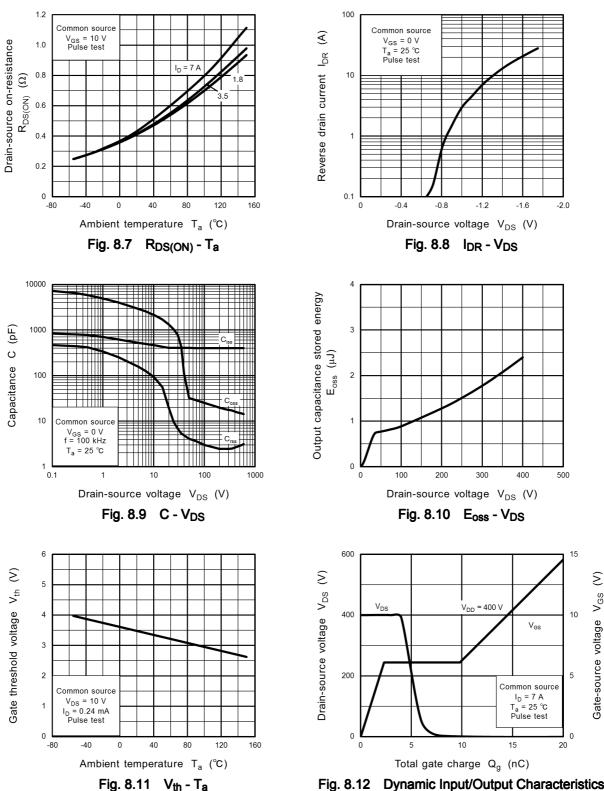


Fig. 8.12 Dynamic Input/Output Characteristics

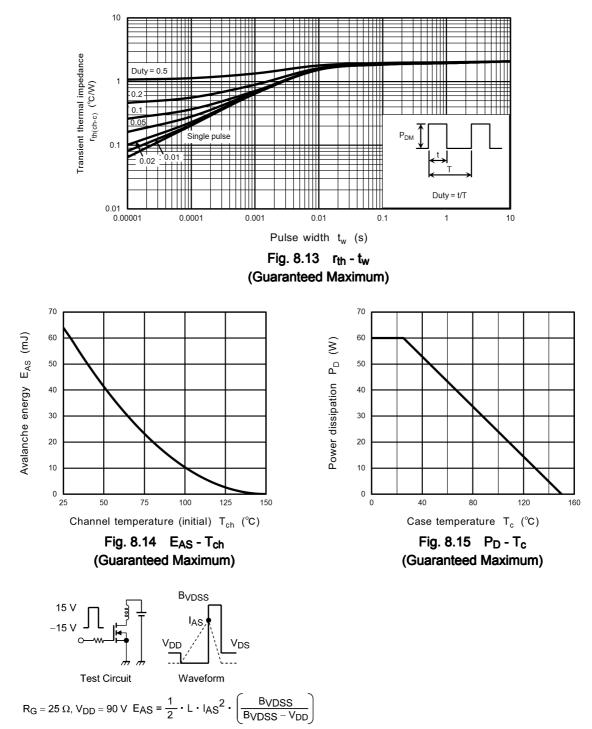
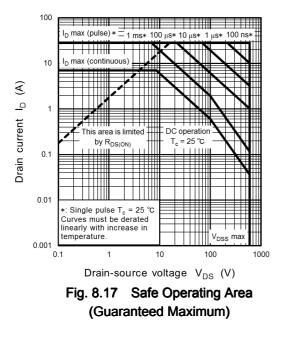


Fig. 8.16 Test Circuit/Waveform



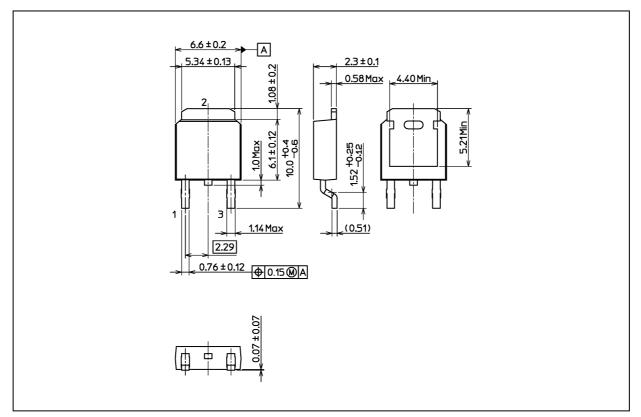
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



TK560P60Y

Package Dimensions

Unit: mm



Weight: 0.36 g (typ.)

	Package Name(s)	
TOSHIBA: 2-7K1S		
Nickname: DPAK		

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